

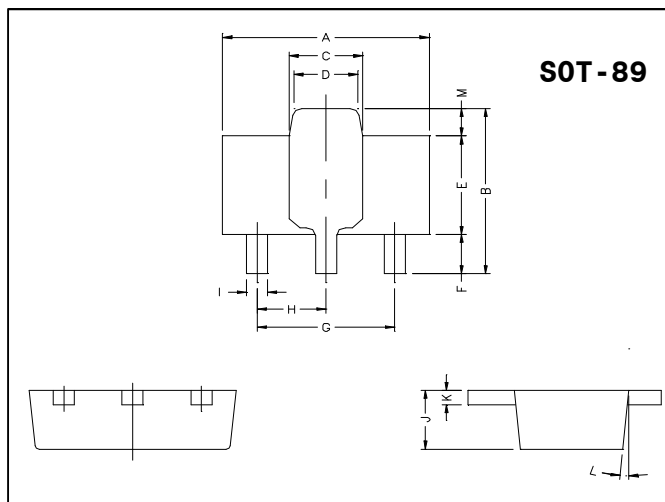
GM2222A

NPN EPITAXIAL PLANAR TRANSISTOR

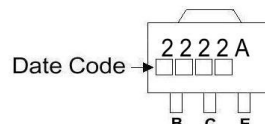
Description

The GM2222A is designed for general purpose amplifier and high speed, medium-power switching applications.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

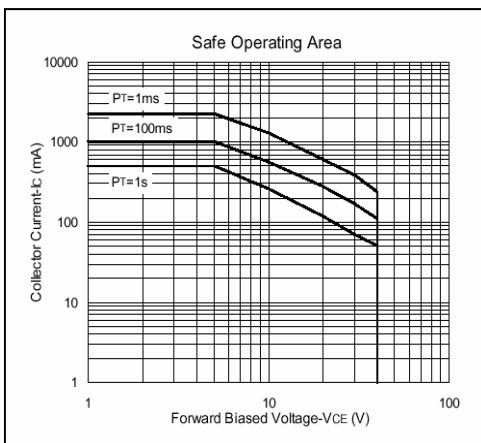
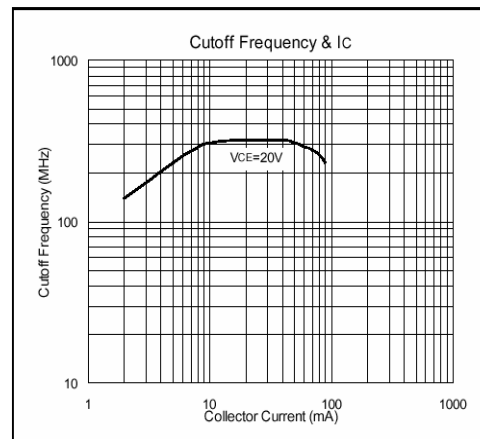
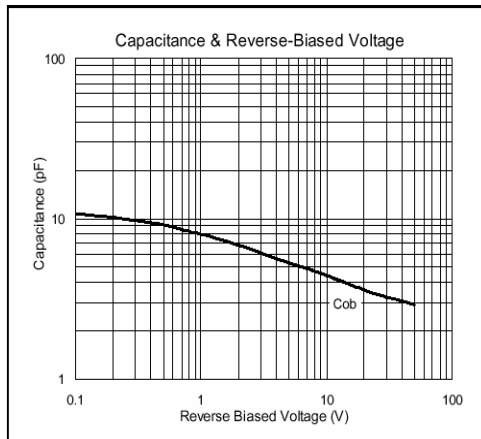
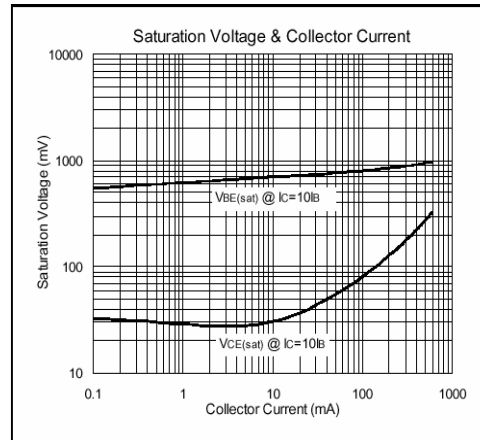
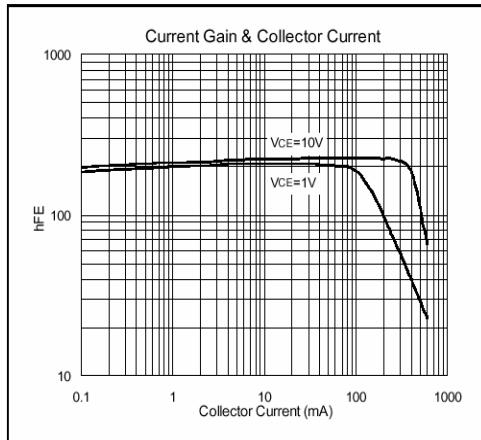
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	75	V
Collector to Emitter Voltage	V _{CE0}	40	V
Emitter to Base Voltage	V _{EB0}	6.0	V
Collector Current	I _C	600	mA
Total Power Dissipation	PD	1.2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	75	-	-	V	I _C =10uA
BV _{CE0}	40	-	-	V	I _C =10mA
BV _{EB0}	6	-	-	V	I _E =10uA
IC _{B0}	-	-	10	nA	V _{CB} =60V
IC _{EX}	-	-	10	nA	V _{CB} =60V, V _{EB} (off)=3V
IE _{B0}	-	-	50	nA	V _{EB} =3V
V _{CE} (sat)1	-	-	300	mV	I _C =150mA, I _B =15mA
V _{CE} (sat)2	-	-	1	V	I _C =500mA, I _B =50mA
V _{BE} (sat)1	-	-	1.2	V	I _C =150mA, I _B =15mA
V _{BE} (sat)2	-	-	2	V	I _C =500mA, I _B =50mA
h _{FE} 1	35	-	-		V _{CE} =10V, I _C =100uA
h _{FE} 2	50	-	-		V _{CE} =10V, I _C =1mA
h _{FE} 3	75	-	-		V _{CE} =10V, I _C =10mA
h _{FE} 4	100	-	300		V _{CE} =10V, I _C =150mA
h _{FE} 5	40	-	-		V _{CE} =10V, I _C =500mA
h _{FE} 6	50	-	-		V _{CE} =1V, I _C =150mA
f _T	300	-	-	MHz	V _{CE} =20V, I _C =20mA, f=100MHz

Characteristics Curve



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